



Product data sheet

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Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
PD	Power Dissipation	150	mW
Тѕтс	Storage Temperature Range	-55 to +125	°C
TJ	Operating Junction Temperature	+125	°C
V _R	Reverse Voltage	85	V
I _{FO}	Forward Current	75	mA

These ratings are limiting values above which the serviceability of the diode may be impaired.

FEATURES

- Fast Switching Speed
- For General Purpose
 Switching Applications
- High Conductance

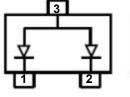
1. Gate

- 2. Source
- 3. Drain

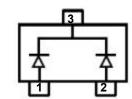


SOT-523

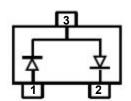
Electrical Symbol & Marking Codes:



BAW56T-MS Marking: JD



BAV70T-MS Marking: JJ



BAV99T-MS Marking: JE

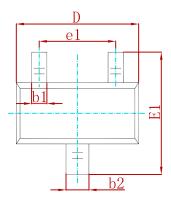
Electrical Characteristics T_A = 25°C unless otherwise noted

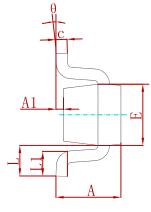
Symbol	Parameter	Test Condition	Limits			Unit
		Test condition	Min	Typical	Max	
V _{BR)}	Reverse Breakdown Voltage	I _R =1µA	85			Volts
I _R	Reverse Leakage Current	V _{R1} =75V			2	μA
		V _{R2} =25V			0.03	
VF	Forward Voltage	I _F =1mA			0.715	
		I⊧=10mA			0.855	Valta
		I⊧=50mA			1.00	Volts
		I⊧=150mA			1.25	
CD	Diode Capacitance	V _R =0V, f=1MHz		1.5	4	pF
Trr	Reverse Recovery Time	I⊧= I₀= 10mA				
		I _{RR} =0.1x			4	ns
		IR,RL=100Ω				

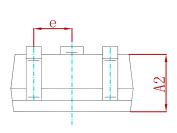




PACKAGE MECHANICAL DATA

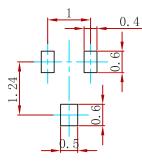






Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
С	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
е	0.500	TYP.	0.020	TYP.
e1	0.900	1.100	0.035	0.043
L	0.400	REF.	0.016	REF.
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

Controlling dimension:in millimeters.
 General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAXXXT-MS	SOT-523	3000





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